

**P-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-30V	-3A	100 @ V _{GS} =-10V
		150 @ V _{GS} =-4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- SOT-23 package.

**ABSOLUTE MAXIMUM RATINGS** (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _A =25°C	-3
		T _A =70°C	-2.4
I _{DM}	-Pulsed ^b	-12	A
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	100	°C/W
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STS3405

Ver 1.1

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.5	-3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V , I _D =-3A		80	100	m ohm
		V _{GS} =-4.5V , I _D =-2.4A		115	150	m ohm
g _{FS}	Forward Transconductance	V _{DS} =-5V , I _D =-3A		8		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V f=1.0MHz		435		pF
C _{OSS}	Output Capacitance			90		pF
C _{RSS}	Reverse Transfer Capacitance			60		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =-15V I _D =-1A V _{GS} =-10V R _{GEN} =6 ohm V _{DS} =-15V, I _D =-3A, V _{GS} =-10V		8		ns
t _r	Rise Time			6.8		ns
t _{D(OFF)}	Turn-Off Delay Time			37		ns
t _f	Fall Time			13		ns
Q _g	Total Gate Charge			7.8		nC
Q _{gs}	Gate-Source Charge		0.58		nC	
Q _{gd}	Gate-Drain Charge		2.2		nC	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _S	Maximum Continuous Drain-Source Diode Forward Current				-1.25	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _S =-1.25A		-0.8	-1.25	V

Notes

- a.Surface Mounted on FR4 Board, t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.

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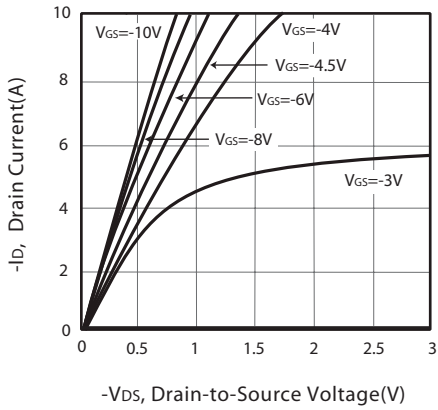


Figure 1. Output Characteristics

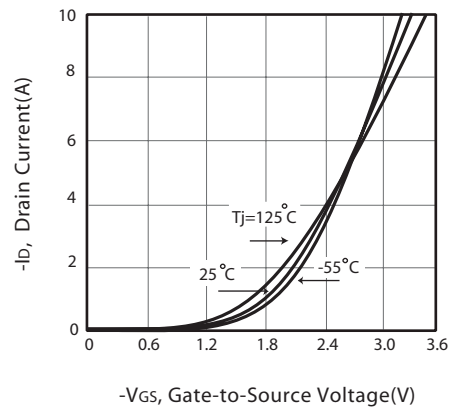


Figure 2. Transfer Characteristics

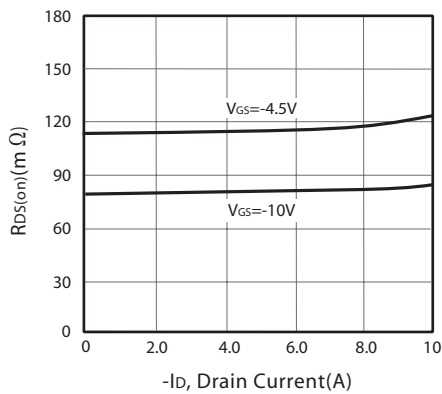


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

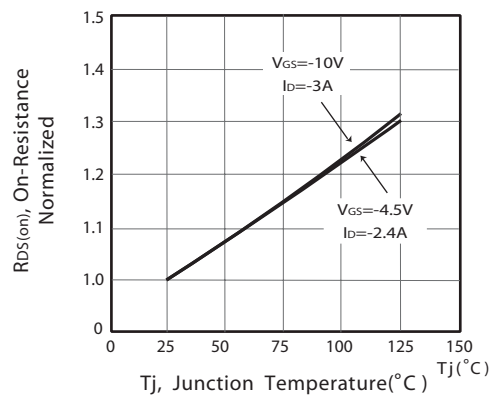


Figure 4. On-Resistance Variation with Drain Current and Temperature

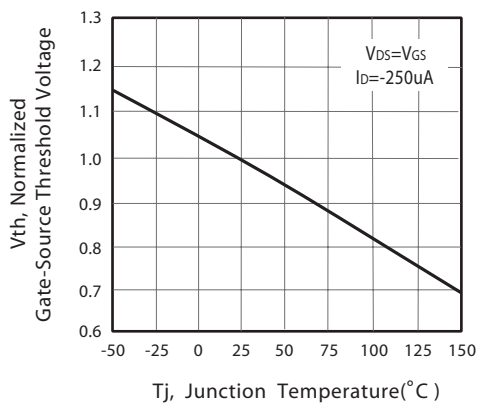


Figure 5. Gate Threshold Variation with Temperature

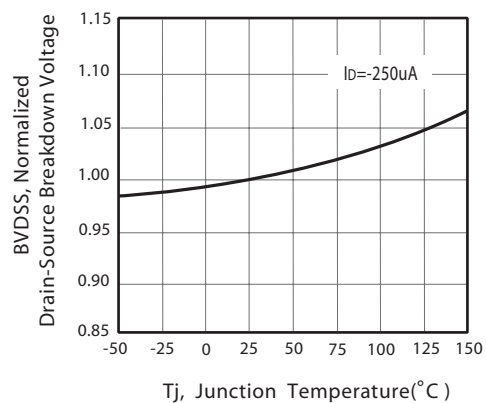


Figure 6. Breakdown Voltage Variation with Temperature

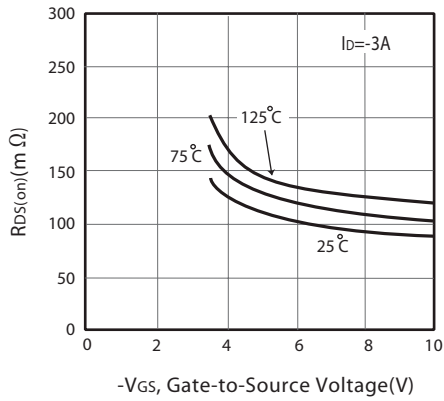


Figure 7. On-Resistance vs. Gate-Source Voltage

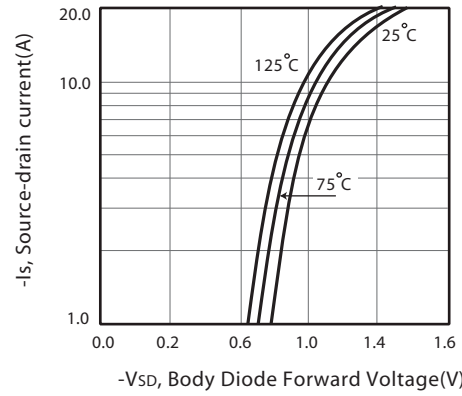


Figure 8. Body Diode Forward Voltage Variation with Source Current

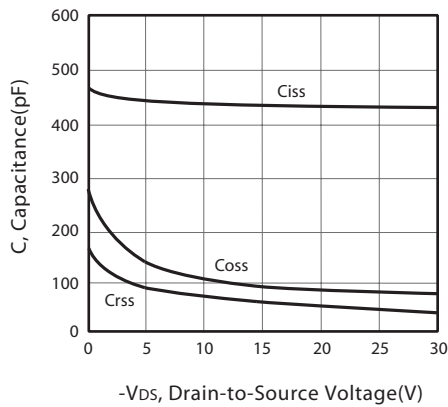


Figure 9. Capacitance

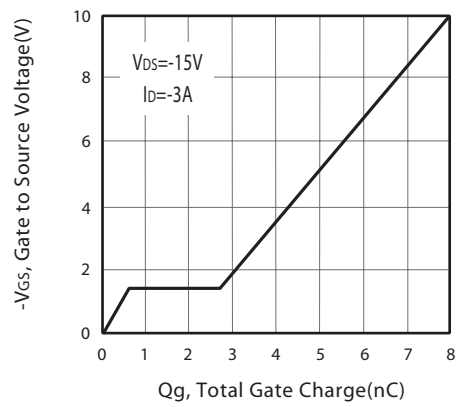


Figure 10. Gate Charge

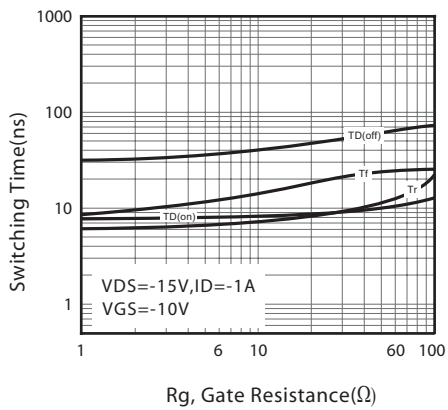


Figure 11. switching characteristics

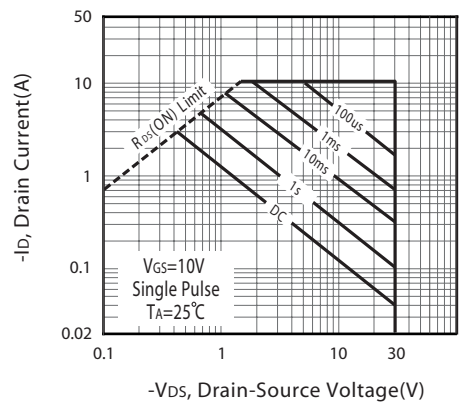


Figure 12. Maximum Safe Operating Area

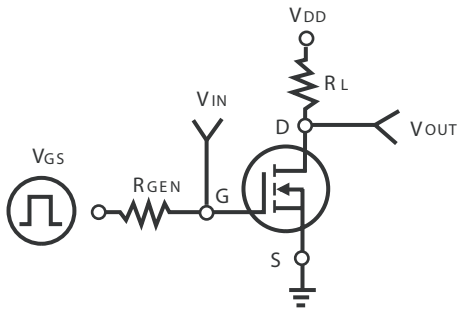


Figure 13. Switching Test Circuit

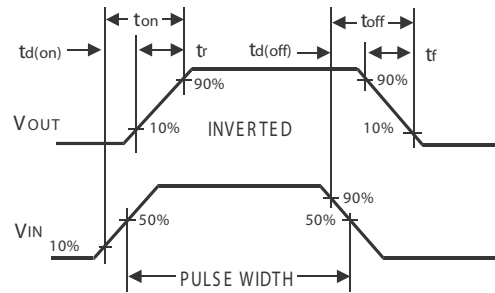
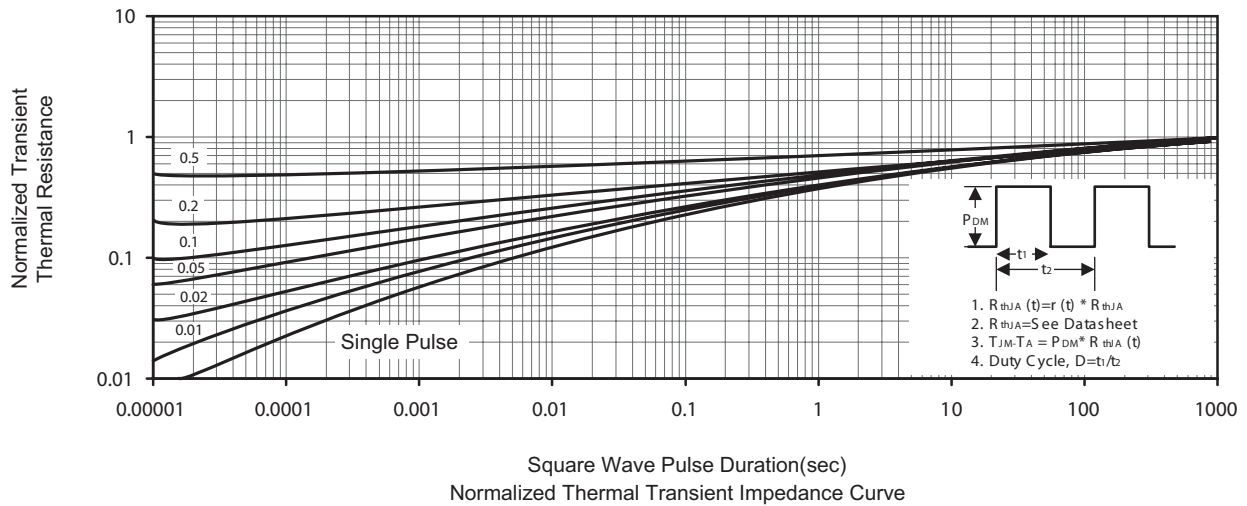
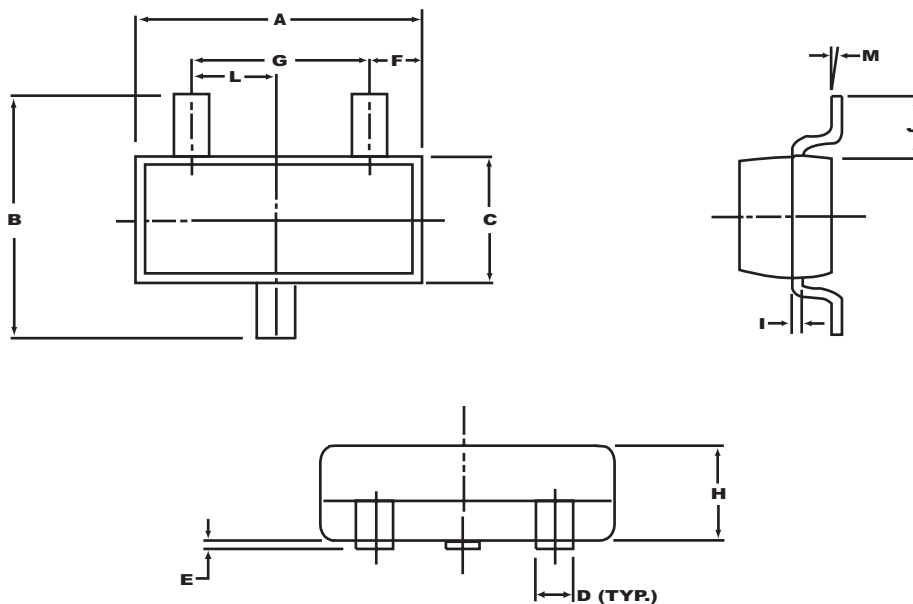


Figure 14. Switching Waveforms



PACKAGE OUTLINE DIMENSIONS

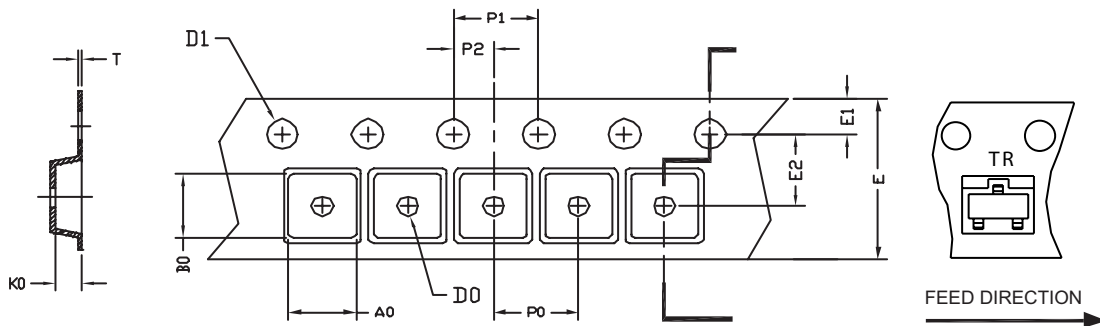
SOT 23



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.106	0.122
B	2.40	2.80	0.094	0.110
C	1.40	1.60	0.055	0.063
D	0.35	0.50	0.014	0.020
E	0	0.10	0	0.004
F	0.45	0.55	0.018	0.022
G	1.90 REF.		0.075 REF.	
H	1.00	1.30	0.039	0.051
I	0.10	0.20	0.004	0.008
J	0.40	-	0.016	-
L	0.45	1.15	0.033	0.045
M	0°	10°	0°	10°

SOT-23 Tape and Reel Data

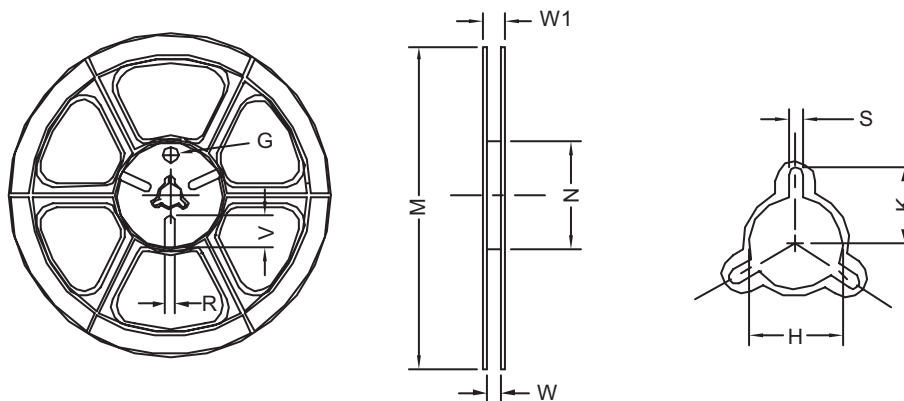
SOT-23 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23	3.20 ± 0.10	3.00 ± 0.10	1.33 ± 0.10	ϕ 1.00 $+0.25$	ϕ 1.50 $+0.10$	8.00 $+0.30$ -0.10	1.75 ± 0.10	3.50 ± 0.05	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.20 ± 0.02

SOT-23 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	ϕ 178	ϕ 178 ± 1	ϕ 60 ± 1	9.00 ± 0.5	12.00 ± 0.5	ϕ 13.5 ± 0.5	10.5	2.00 ± 0.5	ϕ 10.0	5.00	18.00